

X04xxxF

THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R _{th(j-a)}	Junction to ambient	100	°C/W
R _{th(j-c)}	Junction to case for DC	7.5	°C/W

GATE CHARACTERISTICS

P_{G (AV)}= 0.2 W max. P_{GM} = 3 W max. (t_p = 20 µs) I_{GM} = 1.2 A max. (t_p = 20 µs)
V_{GD} = 0.1V min. (V_D=V_{DRM} R_L=3.3kΩ R_{GK} = 1 KΩ T_j= 125 °C)

ELECTRICAL CHARACTERISTICS

Symbol	Test Conditions	Sensitivity			Unit		
		02	03	05			
I _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MIN	20	20	µA	
			MAX	200	200		
V _{GT}	V _D =12V (DC) R _L =140Ω	T _j = 25°C	MAX	0.8		V	
V _{RGM}	I _{RG} =10µA	T _j = 25°C	MIN	8		V	
I _H	I _T = 50mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	5		mA	
I _L	I _G =1mA R _{GK} = 1 KΩ	T _j = 25°C	MAX	6		mA	
V _{TM}	I _{TM} = 8A t _p = 380µs	T _j = 25°C	MAX	1.8		V	
I _{DRM} I _{RRM}	V _D = V _{DRM} R _{GK} = 1 KΩ V _R = V _{RRM}	T _j = 25°C	MAX	5	µA		
		T _j = 110°C	MAX	200			
dV/dt	V _D =67%V _{DRM} R _{GK} = 1 KΩ	T _j = 110°C	MIN	10	15	15	V/µs

ORDERING INFORMATION

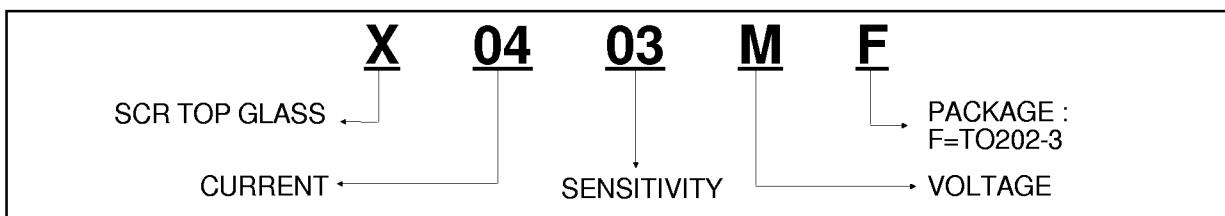


Fig.1 : Maximum average power dissipation versus average on-state current.

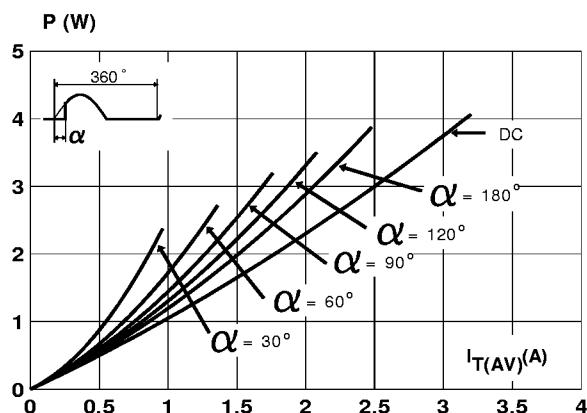


Fig.2 : Correlation between maximum average power dissipation and maximum allowable temperature (Tamb and Tcase).

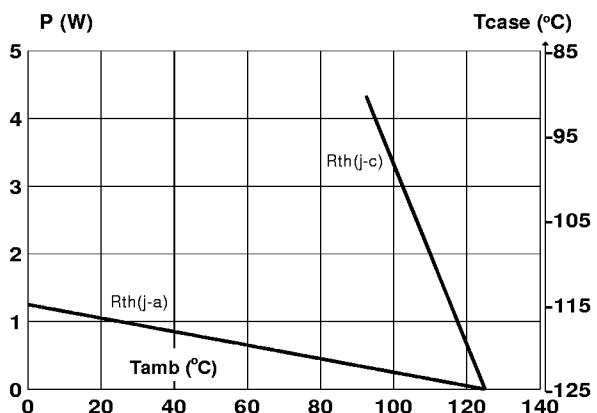


Fig.3 : Average on-state current versus case temperature.

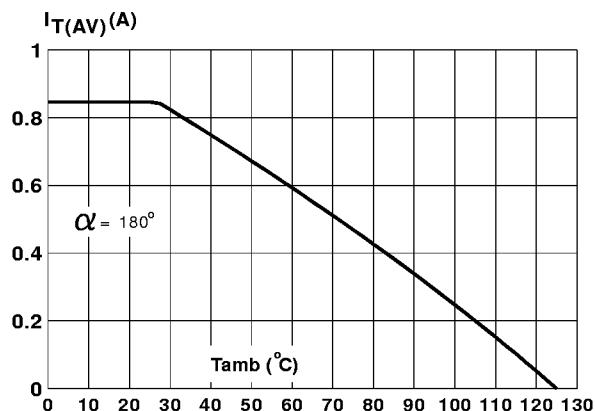


Fig.4 : Relative variation of thermal impedance junction to ambient versus pulse duration.

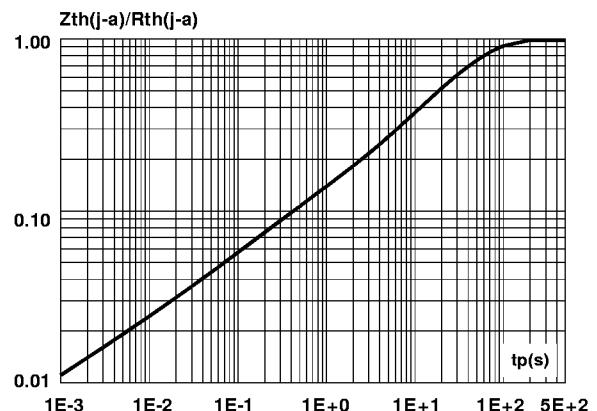


Fig.5 : Relative variation of gate trigger current and holding current versus junction temperature.

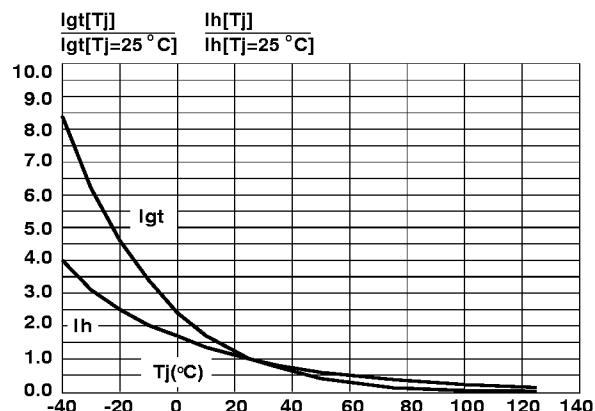
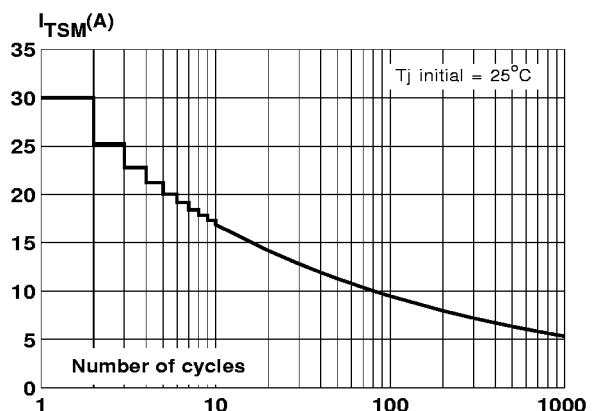


Fig.6 : Non repetitive surge peak on-state current versus number of cycles.



X04xxxF

Fig.7 : Non repetitive surge peak on-state current for a sinusoidal pulse with width : $t_p \leq 10\text{ms}$, and corresponding value of I^2t .

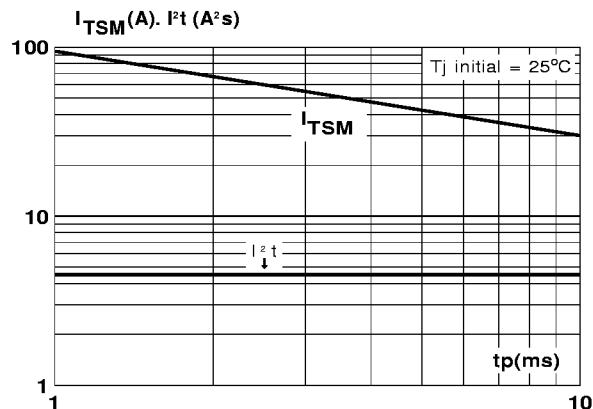
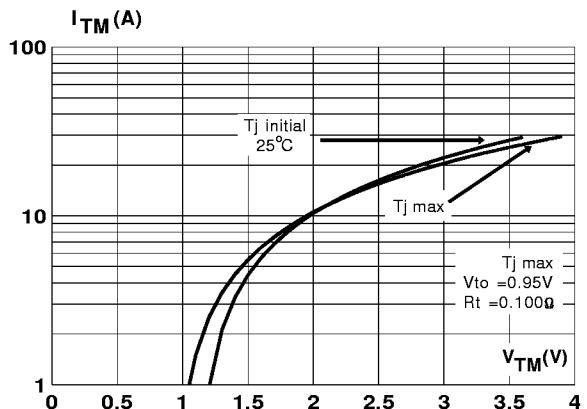


Fig.8 : On-state characteristics (maximum values).



PACKAGE MECHANICAL DATA TO202-3 (Plastic)

REF.	DIMENSIONS			
	Millimeters		Inches	
	Typ.	Max.	Typ.	Max.
A		10.1		0.398
C	7.3		0.287	
D	10.5		0.413	
E	7.4		0.290	
F		1.5		0.059
H	0.51		0.020	
J	1.5		0.059	
M	4.5		0.177	
N		5.3		0.209
N1	2.54		0.100	
O		1.4		0.055
P		0.7		0.028

Marking : type number

Weight : 1 g

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